



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

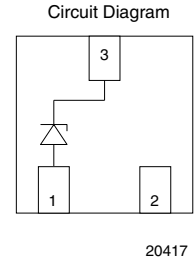
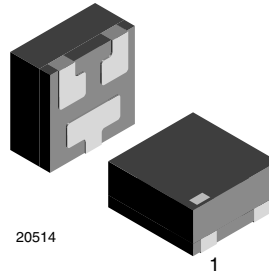




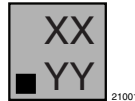
## Single-Line ESD-Protection in LLP75

### Features

- Single-line ESD-protection device
- ESD-immunity acc. IEC 61000-4-2
  - ± 30 kV contact discharge
  - ± 30 kV air discharge
- Space saving LLP package
- Lead (Pb)-free component
- Lead finish = "e3" = matte tin (Sn)
- Non-magnetic
- "Green" molding compound
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



### Marking (example only)



Dot = Pin 1 marking  
 XX = Date code  
 YY = Type code (see table below)

### Ordering Information

Device name	Ordering code	Taped units per reel (8 mm tape on 7" reel)	Minimum order quantity
GSOT03-HT3	GSOT03-HT3-GS08	3000	15000
GSOT04-HT3	GSOT04-HT3-GS08	3000	15000
GSOT05-HT3	GSOT05-HT3-GS08	3000	15000
GSOT08-HT3	GSOT08-HT3-GS08	3000	15000
GSOT12-HT3	GSOT12-HT3-GS08	3000	15000
GSOT15-HT3	GSOT15-HT3-GS08	3000	15000
GSOT24-HT3	GSOT24-HT3-GS08	3000	15000
GSOT36-HT3	GSOT36-HT3-GS08	3000	15000

### Package Data

Device name	Package name	Marking code	Weight	Molding compound flammability rating	Moisture sensitivity level	Soldering conditions
GSOT03-HT3	LLP75-3B	A3	5.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals
GSOT04-HT3	LLP75-3B	A4	5.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals
GSOT05-HT3	LLP75-3B	A5	5.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals
GSOT08-HT3	LLP75-3B	A6	5.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals
GSOT12-HT3	LLP75-3B	A7	5.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals
GSOT15-HT3	LLP75-3B	A8	5.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals
GSOT24-HT3	LLP75-3B	A9	5.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals
GSOT36-HT3	LLP75-3B	AA	5.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals

# GSOT03-HT3 to GSOT36-HT3



Vishay Semiconductors

## Absolute Maximum Ratings GSOT03-HT3

Rating	Test condition	Symbol	Value	Unit
Peak pulse current	Pin 3 to 1 Acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$ ; single shot	$I_{PPM}$	30	A
Peak pulse power	Pin 3 to 1 Acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$ ; single shot	$P_{PP}$	369	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
Operating temperature	Junction temperature	$T_J$	- 40 to + 125	$^{\circ}\text{C}$
Storage temperature		$T_{STG}$	- 55 to + 150	$^{\circ}\text{C}$

## GSOT04-HT3

Rating	Test condition	Symbol	Value	Unit
Peak pulse current	Pin 3 to 1 Acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$ ; single shot	$I_{PPM}$	30	A
Peak pulse power	Pin 3 to 1 Acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$ ; single shot	$P_{PP}$	429	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
Operating temperature	Junction temperature	$T_J$	- 40 to + 125	$^{\circ}\text{C}$
Storage temperature		$T_{STG}$	- 55 to + 150	$^{\circ}\text{C}$

## GSOT05-HT3

Rating	Test condition	Symbol	Value	Unit
Peak pulse current	Pin 3 to 1 Acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$ ; single shot	$I_{PPM}$	30	A
Peak pulse power	Pin 3 to 1 Acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$ ; single shot	$P_{PP}$	480	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
Operating temperature	Junction temperature	$T_J$	- 40 to + 125	$^{\circ}\text{C}$
Storage temperature		$T_{STG}$	- 55 to + 150	$^{\circ}\text{C}$

## GSOT08-HT3

Rating	Test condition	Symbol	Value	Unit
Peak pulse current	Pin 3 to 1 Acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$ ; single shot	$I_{PPM}$	18	A
Peak pulse power	Pin 3 to 1 Acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$ ; single shot	$P_{PP}$	345	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
Operating temperature	Junction temperature	$T_J$	- 40 to + 125	$^{\circ}\text{C}$
Storage temperature		$T_{STG}$	- 55 to + 150	$^{\circ}\text{C}$



## GSOT12-HT3

Rating	Test condition	Symbol	Value	Unit
Peak pulse current	Pin 3 to 1 Acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$ ; single shot	$I_{PPM}$	12	A
Peak pulse power	Pin 3 to 1 Acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$ ; single shot	$P_{PP}$	312	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
Operating temperature	Junction temperature	$T_J$	- 40 to + 125	$^{\circ}\text{C}$
Storage temperature		$T_{STG}$	- 55 to + 150	$^{\circ}\text{C}$

## GSOT15-HT3

Rating	Test condition	Symbol	Value	Unit
Peak pulse current	Pin 3 to 1 Acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$ ; single shot	$I_{PPM}$	8	A
Peak pulse power	Pin 3 to 1 Acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$ ; single shot	$P_{PP}$	230	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
Operating temperature	Junction temperature	$T_J$	- 40 to + 125	$^{\circ}\text{C}$
Storage temperature		$T_{STG}$	- 55 to + 150	$^{\circ}\text{C}$

## GSOT24-HT3

Rating	Test condition	Symbol	Value	Unit
Peak pulse current	Pin 3 to 1 Acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$ ; single shot	$I_{PPM}$	5	A
Peak pulse power	Pin 3 to 1 Acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$ ; single shot	$P_{PP}$	235	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
Operating temperature	Junction temperature	$T_J$	- 40 to + 125	$^{\circ}\text{C}$
Storage temperature		$T_{STG}$	- 55 to + 150	$^{\circ}\text{C}$

## GSOT36-HT3

Rating	Test condition	Symbol	Value	Unit
Peak pulse current	Pin 3 to 1 Acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$ ; single shot	$I_{PPM}$	3.5	A
Peak pulse power	Pin 3 to 1 Acc. IEC 61000-4-5, $t_p = 8/20 \mu\text{s}$ ; single shot	$P_{PP}$	248	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
Operating temperature	Junction temperature	$T_J$	- 40 to + 125	$^{\circ}\text{C}$
Storage temperature		$T_{STG}$	- 55 to + 150	$^{\circ}\text{C}$

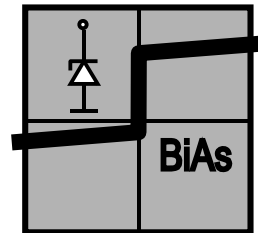
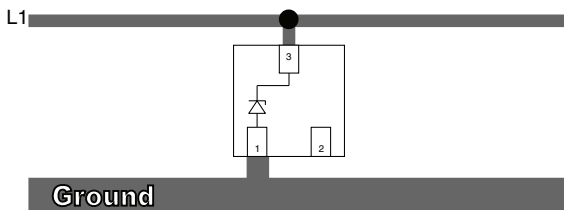
## BiAs-Mode (1-line Bidirectional Asymmetrical protection mode)

With the **GSOTxx-HT3** one signal- or data-lines (L1) can be protected against voltage transients. With pin 1 connected to ground and pin 3 connected to a signal- or data-line which has to be protected. As long as the voltage level on the data- or signal-line is between 0 V (ground level) and the specified **Maximum Reverse Working Voltage** ( $V_{RWM}$ ) the protection diode between pin 2 and pin 3 offer a high isolation to the ground line. The protection device behaves like an open switch.

As soon as any positive transient voltage signal exceeds the break through voltage level of the protection diode, the diode becomes conductive and shorts the transient current to ground. Now the protection device behaves like a closed switch. The **Clamping Voltage** ( $V_C$ ) is defined by the **Breakthrough Voltage** ( $V_{BR}$ ) level plus the voltage drop at the series impedance (resistance and inductance) of the protection device.

Any negative transient signal will be clamped accordingly. The negative transient current is flowing in the forward direction of the protection diode. The low **Forward Voltage** ( $V_F$ ) clamps the negative transient close to the ground level.

Due to the different clamping levels in forward and reverse direction the **GSOTxx-HT3** clamping behaviour is **Bidirectional** and **Asymmetrical (BiAs)**.



20418

## Electrical Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified

### GSOT03-HT3

BiAs mode (between pin 3 to 1)

Parameter	Test conditions/remarks	Symbol	Min.	Typ.	Max.	Unit
Protection paths	Number of lines which can be protected	$N_{lines}$			1	lines
Reverse stand off voltage	at $I_R = 100 \mu A$	$V_{RWM}$	3.3			V
Reverse current	at $V_R = 3.3 V$	$I_R$			100	$\mu A$
Reverse break down voltage	at $I_R = 1 mA$	$V_{BR}$	4	4.6		V
Reverse clamping voltage	at $I_{PP} = 1 A$	$V_C$		5.7	7.5	V
	at $I_{PP} = I_{PPM} = 30 A$	$V_C$		10	12.3	V
Forward clamping voltage	at $I_{PP} = 1 A$	$V_F$		1	1.2	V
	at $I_{PP} = I_{PPM} = 30 A$	$V_F$		4.5		V
Capacitance	at $V_R = 0 V$ ; $f = 1 MHz$	$C_D$		420	600	pF
	at $V_R = 1.6 V$ ; $f = 1 MHz$	$C_D$		260		pF



## GSOT04-HT3

BiAs mode (between pin 3 to 1)

Parameter	Test conditions/remarks	Symbol	Min.	Typ.	Max.	Unit
Protection paths	Number of lines which can be protected	$N_{lines}$			1	lines
Reverse stand off voltage	at $I_R = 20 \mu A$	$V_{RWM}$	4			V
Reverse current	at $V_R = 4 V$	$I_R$			20	$\mu A$
Reverse break down voltage	at $I_R = 1 mA$	$V_{BR}$	5	6.1		V
Reverse clamping voltage	at $I_{PP} = 1 A$	$V_C$		7.5	9	V
	at $I_{PP} = I_{PPM} = 30 A$	$V_C$		11.2	14.3	V
Forward clamping voltage	at $I_{PP} = 1 A$	$V_F$		1	1.2	V
	at $I_{PP} = I_{PPM} = 30 A$	$V_F$		4.5		V
Capacitance	at $V_R = 0 V$ ; $f = 1 MHz$	$C_D$		310	450	pF
	at $V_R = 2 V$ ; $f = 1 MHz$	$C_D$		200		pF

## GSOT05-HT3

BiAs mode (between pin 3 to 1)

Parameter	Test conditions/remarks	Symbol	Min.	Typ.	Max.	Unit
Protection paths	Number of lines which can be protected	$N_{lines}$			1	lines
Reverse stand off voltage	at $I_R = 10 \mu A$	$V_{RWM}$	5			V
Reverse current	at $V_R = 5 V$	$I_R$			10	$\mu A$
Reverse break down voltage	at $I_R = 1 mA$	$V_{BR}$	6	6.8		V
Reverse clamping voltage	at $I_{PP} = 1 A$	$V_C$		7	8.7	V
	at $I_{PP} = I_{PPM} = 30 A$	$V_C$		12	16	V
Forward clamping voltage	at $I_{PP} = 1 A$	$V_F$		1	1.2	V
	at $I_{PP} = I_{PPM} = 30 A$	$V_F$		4.5		V
Capacitance	at $V_R = 0 V$ ; $f = 1 MHz$	$C_D$		260	350	pF
	at $V_R = 2.5 V$ ; $f = 1 MHz$	$C_D$		150		pF

## GSOT08-HT3

BiAs mode (between pin 3 to 1)

Parameter	Test conditions/remarks	Symbol	Min.	Typ.	Max.	Unit
Protection paths	Number of lines which can be protected	$N_{lines}$			1	lines
Reverse stand off voltage	at $I_R = 5 \mu A$	$V_{RWM}$	8			V
Reverse current	at $V_R = 8 V$	$I_R$			5	$\mu A$
Reverse break down voltage	at $I_R = 1 mA$	$V_{BR}$	9	10		V
Reverse clamping voltage	at $I_{PP} = 1 A$	$V_C$		10.7	13	V
	at $I_{PP} = I_{PPM} = 18 A$	$V_C$		15.2	19.2	V
Forward clamping voltage	at $I_{PP} = 1 A$	$V_F$		1	1.2	V
	at $I_{PP} = I_{PPM} = 18 A$	$V_F$		3		V
Capacitance	at $V_R = 0 V$ ; $f = 1 MHz$	$C_D$		160	250	pF
	at $V_R = 4 V$ ; $f = 1 MHz$	$C_D$		80		pF

# GSOT03-HT3 to GSOT36-HT3



Vishay Semiconductors

## GSOT12-HT3

BiAs mode (between pin 3 to 1)

Parameter	Test conditions/remarks	Symbol	Min.	Typ.	Max.	Unit
Protection paths	Number of lines which can be protected	$N_{lines}$			1	lines
Reverse stand off voltage	at $I_R = 1 \mu A$	$V_{RWM}$	12			V
Reverse current	at $V_R = 12 V$	$I_R$			1	$\mu A$
Reverse break down voltage	at $I_R = 1 mA$	$V_{BR}$	13.5	15		V
Reverse clamping voltage	at $I_{PP} = 1 A$	$V_C$		15.4	18.7	V
	at $I_{PP} = I_{PPM} = 12 A$	$V_C$		21.2	26	V
Forward clamping voltage	at $I_{PP} = 1 A$	$V_F$		1	1.2	V
	at $I_{PP} = I_{PPM} = 12 A$	$V_F$		2.2		V
Capacitance	at $V_R = 0 V$ ; $f = 1 MHz$	$C_D$		115	150	pF
	at $V_R = 6 V$ ; $f = 1 MHz$	$C_D$		50		pF

## GSOT15-HT3

BiAs mode (between pin 3 to 1)

Parameter	Test conditions/remarks	Symbol	Min.	Typ.	Max.	Unit
Protection paths	Number of lines which can be protected	$N_{lines}$			1	lines
Reverse stand off voltage	at $I_R = 1 \mu A$	$V_{RWM}$	15			V
Reverse current	at $V_R = 15 V$	$I_R$			1	$\mu A$
Reverse break down voltage	at $I_R = 1 mA$	$V_{BR}$	16.5	18		V
Reverse clamping voltage	at $I_{PP} = 1 A$	$V_C$		19.4	23.5	V
	at $I_{PP} = I_{PPM} = 8 A$	$V_C$		24.8	28.8	V
Forward clamping voltage	at $I_{PP} = 1 A$	$V_F$		1	1.2	V
	at $I_{PP} = I_{PPM} = 8 A$	$V_F$		1.8		V
Capacitance	at $V_R = 0 V$ ; $f = 1 MHz$	$C_D$		90	120	pF
	at $V_R = 7.5 V$ ; $f = 1 MHz$	$C_D$		35		pF

## GSOT24-HT3

BiAs mode (between pin 3 to 1)

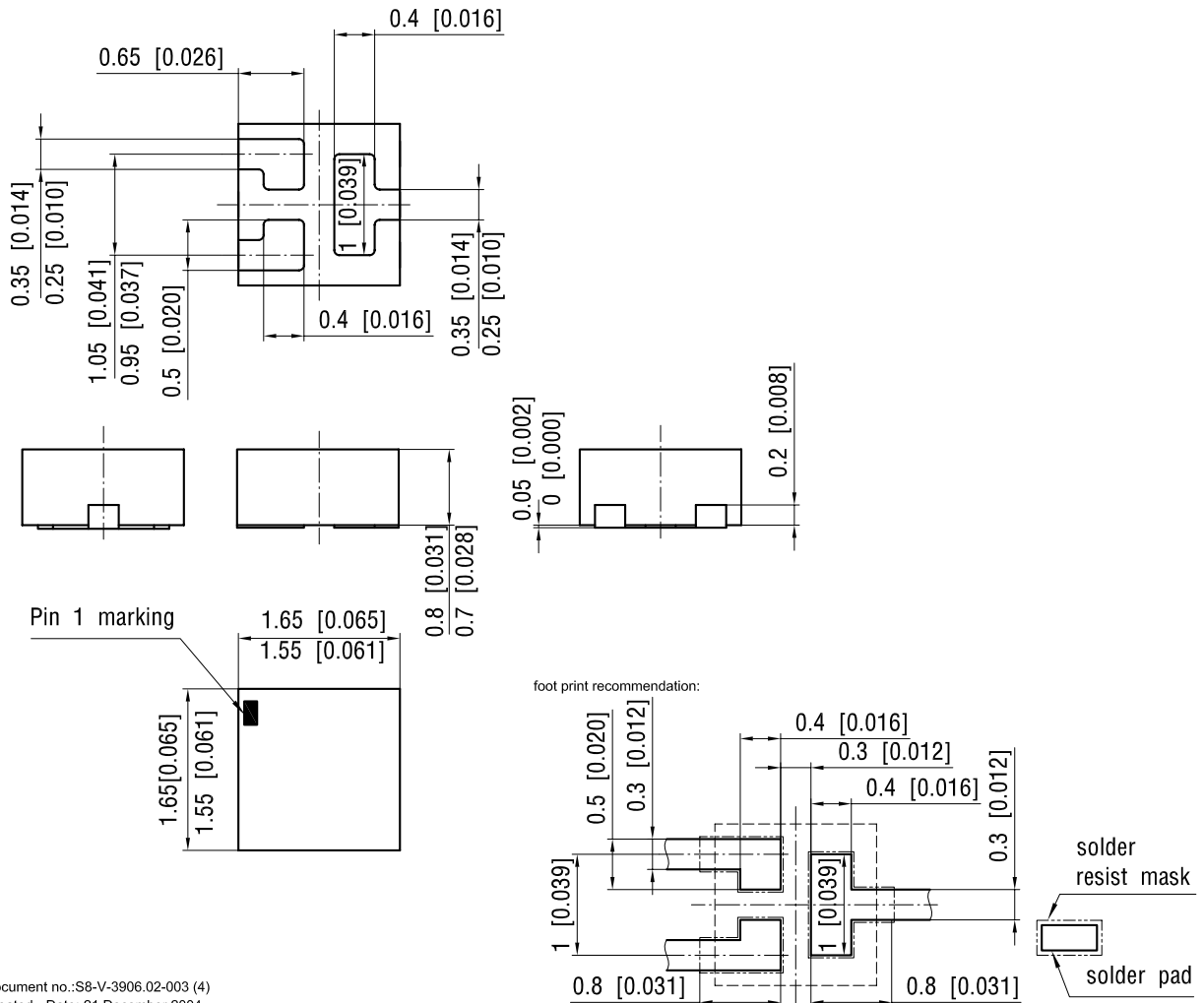
Parameter	Test conditions/remarks	Symbol	Min.	Typ.	Max.	Unit
Protection paths	Number of lines which can be protected	$N_{lines}$			1	lines
Reverse stand off voltage	at $I_R = 1 \mu A$	$V_{RWM}$	24			V
Reverse current	at $V_R = 24 V$	$I_R$			1	$\mu A$
Reverse break down voltage	at $I_R = 1 mA$	$V_{BR}$	27	30		V
Reverse clamping voltage	at $I_{PP} = 1 A$	$V_C$		34	41	V
	at $I_{PP} = I_{PPM} = 5 A$	$V_C$		41	47	V
Forward clamping voltage	at $I_{PP} = 1 A$	$V_F$		1	1.2	V
	at $I_{PP} = I_{PPM} = 5 A$	$V_F$		1.4		V
Capacitance	at $V_R = 0 V$ ; $f = 1 MHz$	$C_D$		65	80	pF
	at $V_R = 12 V$ ; $f = 1 MHz$	$C_D$		20		pF

## GSOT36-HT3

BiAs mode (between pin 3 to 1)

Parameter	Test conditions/remarks	Symbol	Min.	Typ.	Max.	Unit
Protection paths	Number of lines which can be protected	$N_{lines}$			1	lines
Reverse stand off voltage	at $I_R = 1 \mu A$	$V_{RWM}$	36			V
Reverse current	at $V_R = 36 V$	$I_R$			1	$\mu A$
Reverse break down voltage	at $I_R = 1 mA$	$V_{BR}$	39	43		V
Reverse clamping voltage	at $I_{PP} = 1 A$	$V_C$		49	60	V
	at $I_{PP} = I_{PPM} = 3.5 A$	$V_C$		59	71	V
Forward clamping voltage	at $I_{PP} = 1 A$	$V_F$		1	1.2	V
	at $I_{PP} = I_{PPM} = 3.5 A$	$V_F$		1.3		V
Capacitance	at $V_R = 0 V$ ; $f = 1 MHz$	$C_D$		52	65	pF
	at $V_R = 18 V$ ; $f = 1 MHz$	$C_D$		12		pF

### Package Dimensions in millimeters (inches): LLP75-3B



Document no.: S8-V-3906.02-003 (4)  
 Created - Date: 21.December.2004  
 Rev. 2 - Date: 21.March.2006  
 18057

### Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA.
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design  
and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany



### Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.